



A1A:22.XX

VOLTAGE RATINGS

Part Number	V_{RRM} , V_R (V) Max. rep. peak reverse voltage		V_{RSM} , V_R (V) Max. non- rep. peak reverse voltage
	$T_J = 0$ to 180°C	$T_J = -40$ to 0°C	$T_J = 25$ to 180°C
A1A:22.02	200	200	300
A1A:22.04	400	400	500
A1A:22.06	600	600	700
A1A:22.08	800	800	900
A1A:22.10	1000	1000	1100
A1A:22.12	1200	1200	1300
A1A:22.14	1400	1400	1500
A1A:22.16	1600	1600	1700

This datasheet applies to:

**Metric thread: A1A:22.XX,
A1B:22.XX**

**Inch thread: A2A:22.XX,
A2B:22.XX**

MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
T_J Junction Temperature	-40 to 180	$^{\circ}\text{C}$	-
T_{stg} Storage Temperature	-40 to 180	$^{\circ}\text{C}$	-
$I_{F(AV)}$ Max. Av. current @ Max. T_C	22	A	180° half sine wave
	125	$^{\circ}\text{C}$	
$I_{F(RMS)}$ Nom. RMS current	43	A	-
I_{FSM} Max. Peak non-rep. surge current	0.32	kA	50 Hz half cycle sine wave Initial $T_J = 180^{\circ}\text{C}$, rated V_{RRM} applied after surge.
	0.35		60 Hz half cycle sine wave
	0.39		50 Hz half cycle sine wave Initial $T_J = 180^{\circ}\text{C}$, no voltage applied after surge.
	0.42		60 Hz half cycle sine wave
I^2t Max. I^2t capability	0.47	kA^2s	$t = 10\text{ms}$ Initial $T_J = 180^{\circ}\text{C}$, rated V_{RRM} applied after surge.
	0.51		$t = 8.3\text{ ms}$
	0.66		$t = 10\text{ms}$ Initial $T_J = 180^{\circ}\text{C}$, no voltage applied after surge.
	0.72		$t = 8.3\text{ ms}$
$I^2t^{1/2}$ Max. $I^2t^{1/2}$ capability	5.5	$\text{kA}^2\text{s}^{1/2}$	Initial $T_J = 180^{\circ}\text{C}$, no voltage applied after surge. I^2t for time $t_x = I^2t^{1/2} * t_x^{1/2}$. ($0.1 < t_x < 10\text{ms}$).
F Mounting Force	2(~15)	N.m(Lbf.in)	-



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CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_{FM} Peak forward voltage	---	1.35	1.50	V	Initial $T_J = 25^\circ\text{C}$, sinusoidal wave, $I_{peak} = 69\text{A}$.
$V_{F(TO)1}$ Low-level threshold	---	---	0.85	V	$T_J = 180^\circ\text{C}$
$V_{F(TO)2}$ High-level threshold	---	---	1.00		Av. power = $V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$
r_{F1} Low-level resistance	---	---	10.00	m	Use low values for $I_{FM} < I_{F(AV)}$
r_{F2} High-level resistance	---	---	5.00		
I_{RM} Peak reverse current	---	---	3.00	mA	$T_J = 180^\circ\text{C}$. Max. Rated V_{RRM}
R_{thJC} Thermal resistance, junction-to-case	---	---	2.00	$^\circ\text{C/W}$	DC operation
	---	---	2.60	$^\circ\text{C/W}$	180° sine wave
	---	---	2.90	$^\circ\text{C/W}$	120° rectangular wave
R_{thCS} Thermal resistance, case-to-sink	---	---	1.00	$^\circ\text{C/W}$	Mtg. Surface smooth, flat and greased. Single side.
wt Weight	---	9(0.32)	---	g(oz.)	---
Case Style	DO-203AA (DO-4)			JEDEC	---

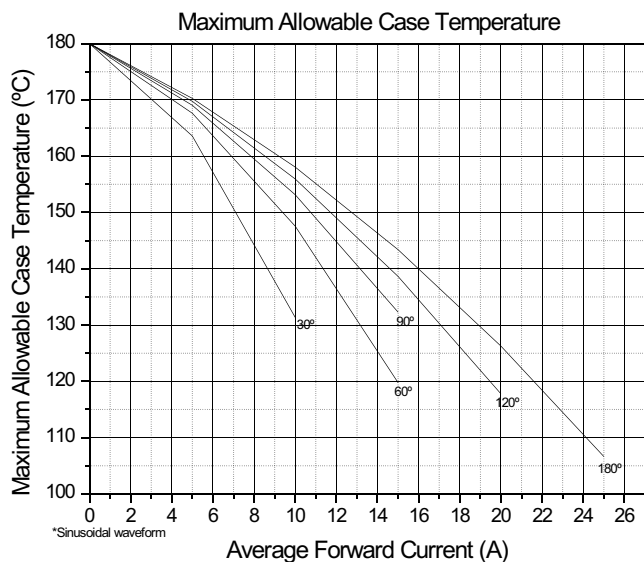


Fig. 1 - Current Ratings Characteristics

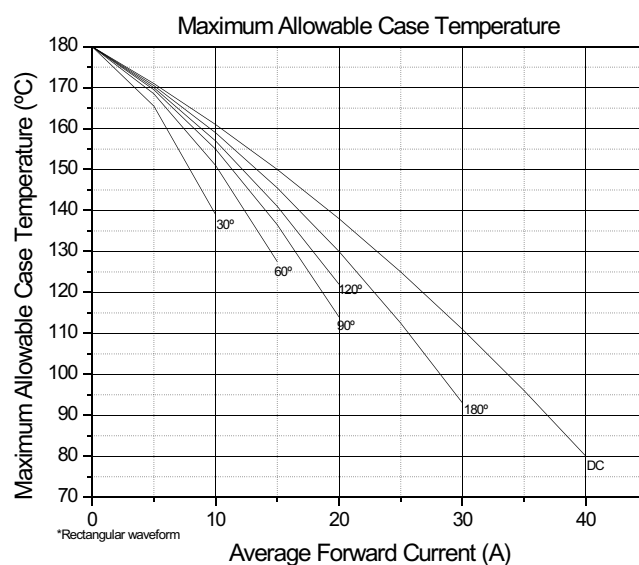


Fig. 2 - Current Ratings Characteristics



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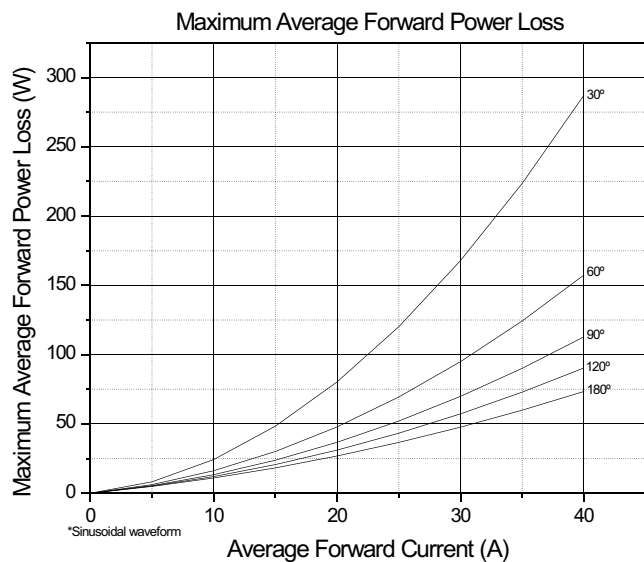


Fig. 3 - On-State Power Loss Characteristics

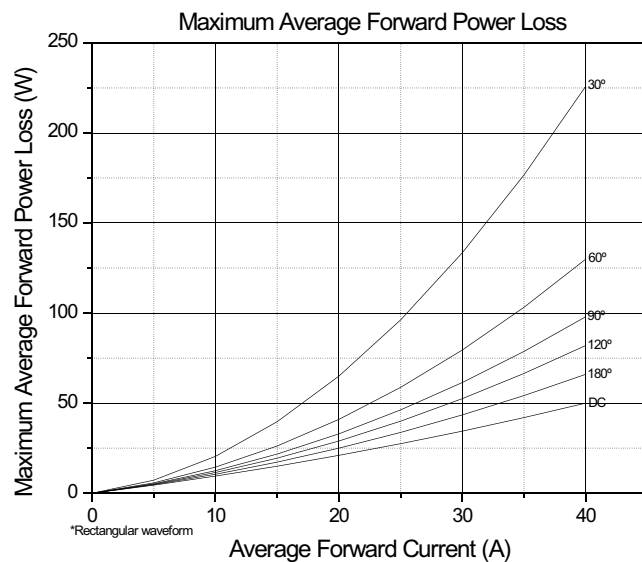


Fig. 4 - On-State Power Loss Characteristics

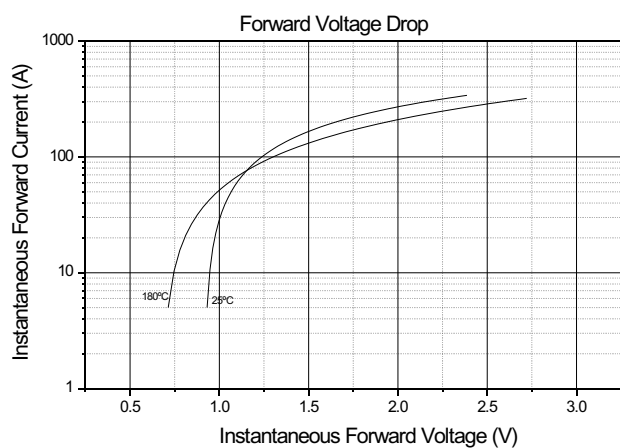


Fig. 5 - Forward Voltage Drop Characteristics

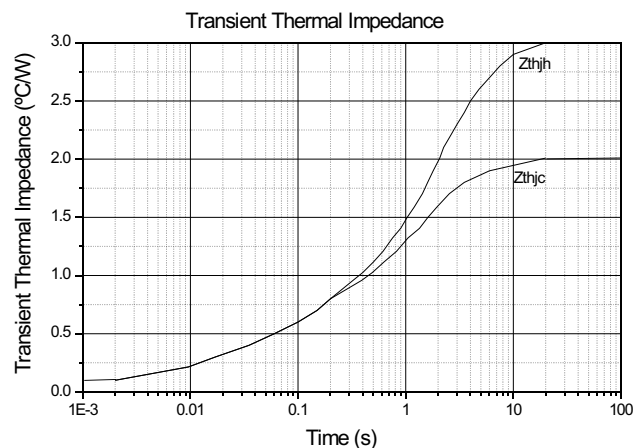


Fig. 6 - Transient Thermal Impedance Characteristics



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SEMICONDUCTORES LTDA.

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DO-203AA (DO-4)

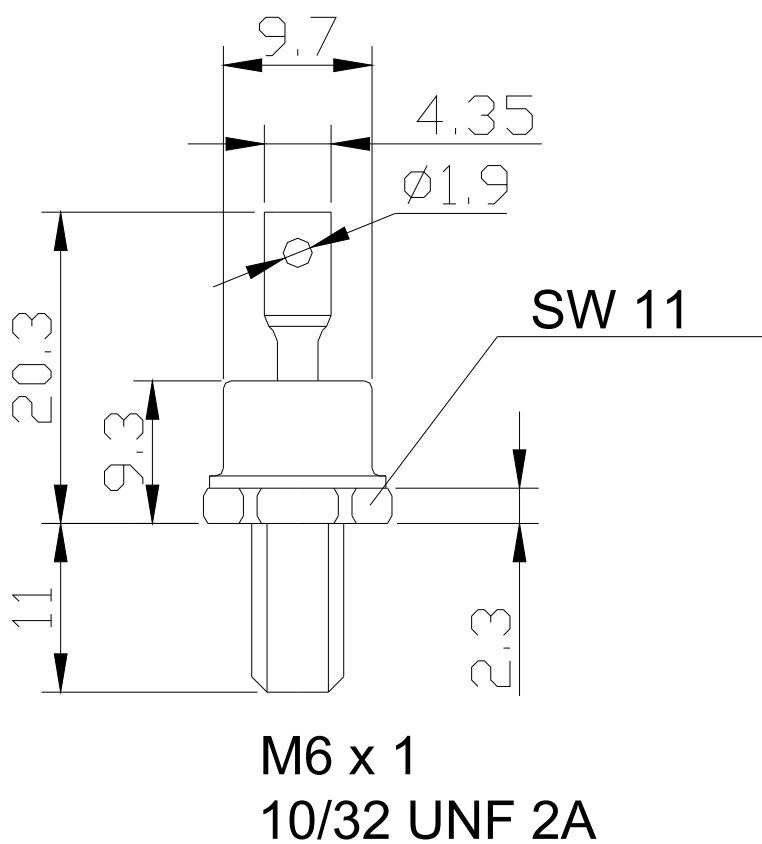


Fig. 7 - Outline Characteristics